

ZXMN3A02X8

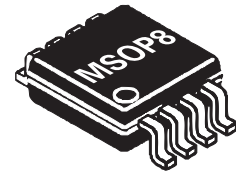
30V N-CANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS}=30V$; $R_{DS(ON)}=0.025\Omega$ $I_D=6.7A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

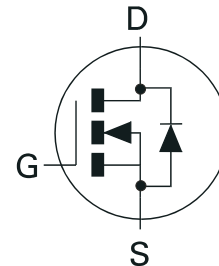


FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

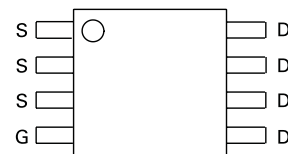
APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Disconnect switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN3A02X8TA	7"	12mm	1000 units
ZXMN3A02X8TC	13"	12mm	4000 units



Top View

DEVICE MARKING

- ZXMN
3A02

ZXMN3A02X8

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	30	V
Gate Source Voltage	V _{GS}	±20	V
Continuous Drain Current V _{GS} =10V; T _A =25°C (b) V _{GS} =10V; T _A =70°C (b) V _{GS} =10V; T _A =25°C (a)	I _D	6.7 5.4 5.3	A
Pulsed Drain Current (c)	I _{DM}	24	A
Continuous Source Current (Body Diode) (b)	I _S	3.2	A
Pulsed Source Current (Body Diode) (c)	I _{SM}	24	A
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	1.1 8.8	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	1.8 14.4	W mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	R _{θJA}	113	°C/W
Junction to Ambient (b)	R _{θJA}	70	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at t ≤ 10 secs.

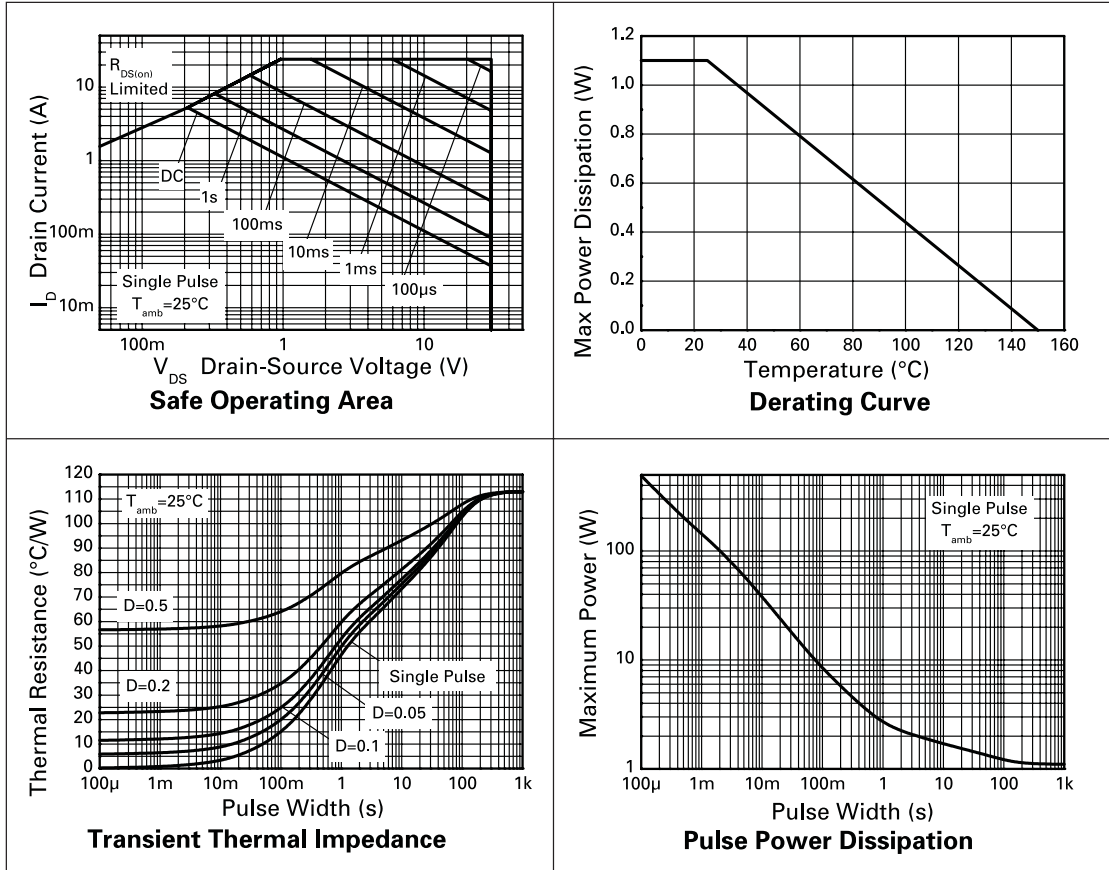
(c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10μs - pulse width limited by maximum junction temperature.



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CHARACTERISTICS



* For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

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ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	30			V	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			1	μA	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1			V	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.025 0.035	Ω Ω	$V_{GS}=10\text{V}, I_D=12\text{A}$ $V_{GS}=4.5\text{V}, I_D=10.2\text{A}$
Forward Transconductance (1)(3)	g_{fs}		22		S	$V_{DS}=10\text{V}, I_D=12\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		1400		pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}$
Output Capacitance	C_{oss}		209		pF	
Reverse Transfer Capacitance	C_{rss}		120		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		3.9		ns	$V_{DD}=15\text{V}, I_D=5.5\text{A}$ $R_G=6.2\Omega, V_{GS}=10\text{V}$ (refer to test circuit)
Rise Time	t_r		5.5		ns	
Turn-Off Delay Time	$t_{d(off)}$		35.0		ns	
Fall Time	t_f		7.6		ns	
Gate Charge	Q_g		14.5		nC	$V_{DS}=15\text{V}, V_{GS}=5\text{V},$ $I_D=5.5\text{A}$ (refer to test circuit)
Total Gate Charge	Q_g		26.8		nC	$V_{DS}=15\text{V}, V_{GS}=10\text{V},$ $I_D=5.5\text{A}$ (refer to test circuit)
Gate-Source Charge	Q_{gs}		4.7		nC	
Gate-Drain Charge	Q_{gd}		4.7		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			0.95	V	$T_J=25^\circ\text{C}, I_S=9\text{A},$ $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	t_{rr}		17		ns	$T_J=25^\circ\text{C}, I_F=5.5\text{A},$ $di/dt= 100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		8.3		nC	

NOTES

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.

(2) Switching characteristics are independent of operating junction temperature.

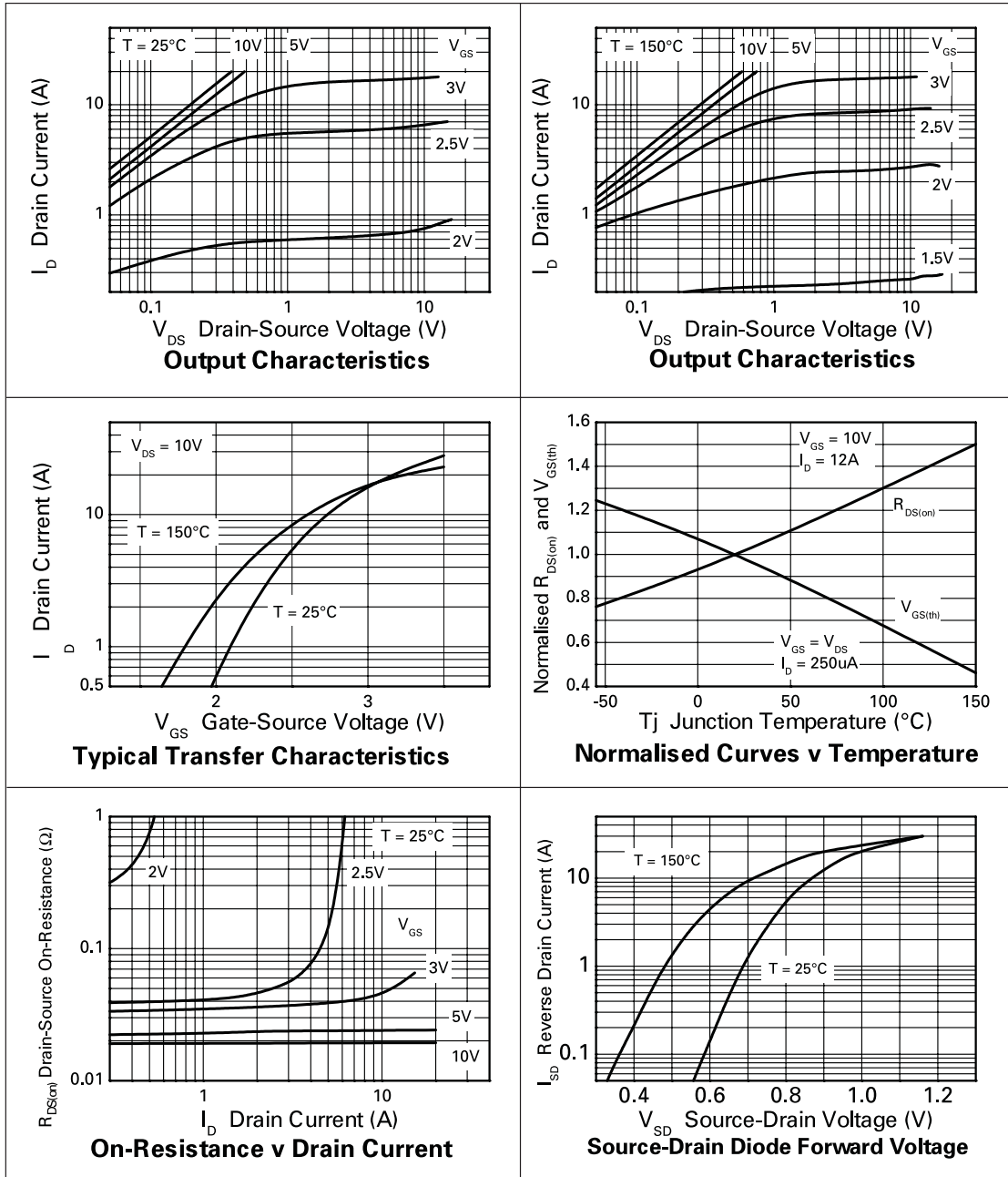
(3) For design aid only, not subject to production testing.



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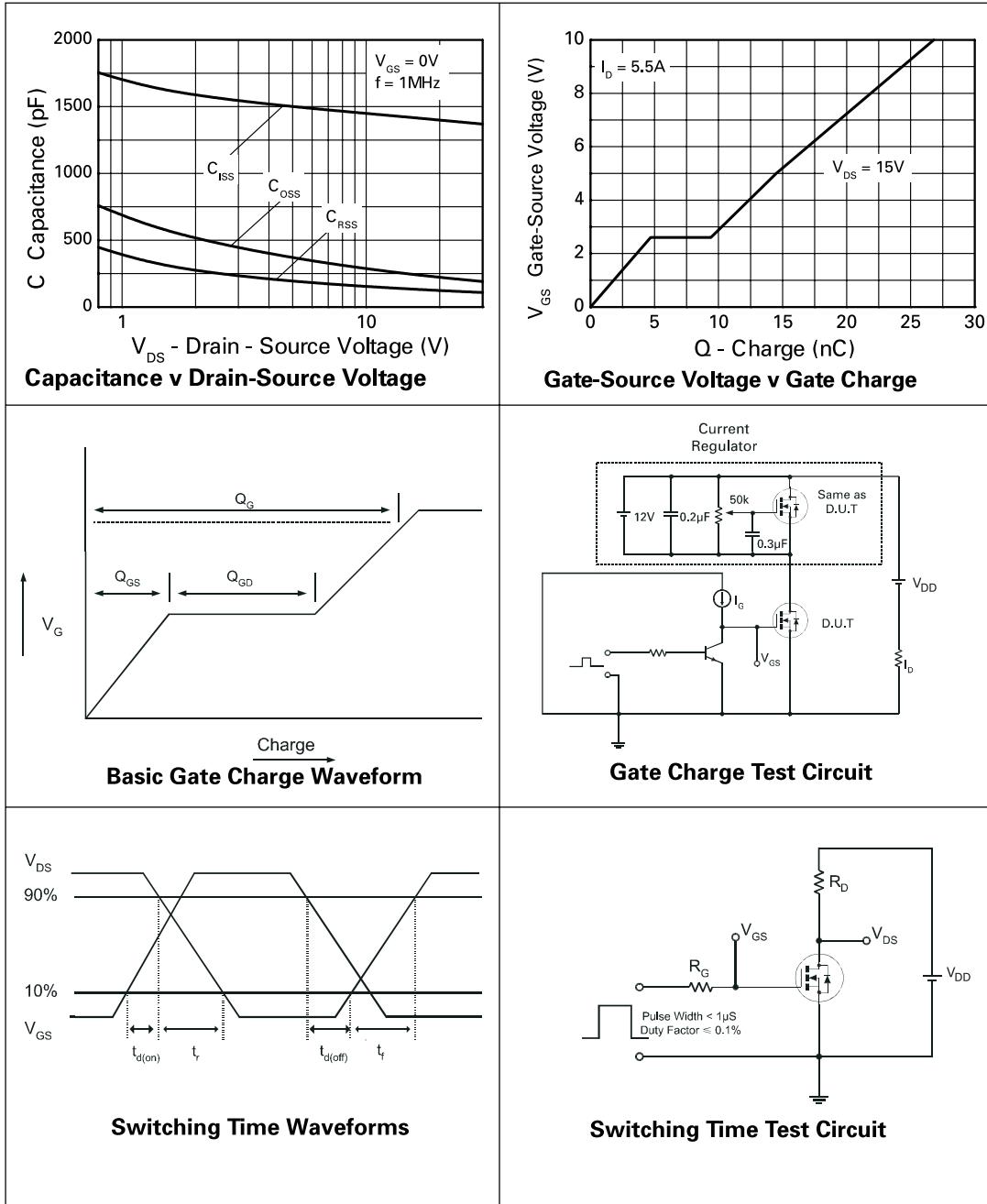
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CHARACTERISTICS



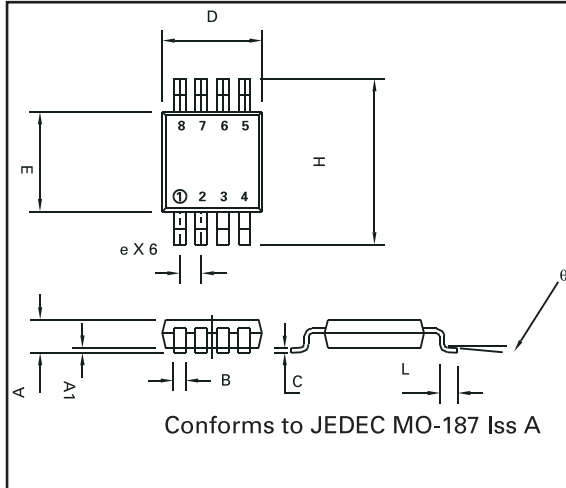
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CHARACTERISTICS



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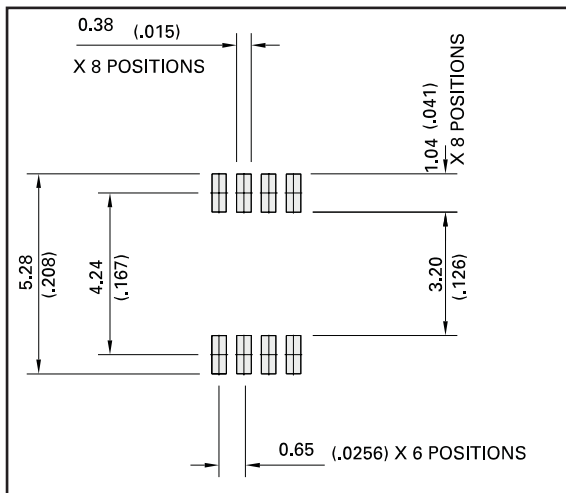
PACKAGE OUTLINE



PACKAGE DIMENSION

DIM	Millimetres		Inches	
	MIN	MAX	MIN	MAX
A		1.10		0.043
A1	0.05	0.15	0.002	0.006
B	0.25	0.40	0.010	0.016
C	0.13	0.23	0.005	0.009
D	2.90	3.10	0.114	0.122
e	0.65	BSC	0.0256	BSC
E	2.90	3.10	0.114	0.122
H	4.90	BSC	0.193	BSC
L	0.40	0.70	0.016	0.028
θ°	0°	6°	0°	6°

PAD LAYOUT



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